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INSULATED GATE TYPE SEMICONDUCTOR DEVICE AND
METHOD FOR FABRICATING SAME

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ABSTRACT OF THE DISCLOSURE

10 An insulated gate type semiconductor device
comprised of a semiconductor layer serving as an active
region isolated from a semiconductor substrate by a
substrate isolation insulating film and a T-shaped gate
electrode comprised of a trunk-shaped main gate electrode
and a crosspiece-shaped conductor pattern provided on the
15 semiconductor layer, wherein the thickness of the gate
insulating film directly under the crosspiece-shaped
conductor pattern is made greater than the thickness of
the gate insulating film directly under the main gate
electrode, whereby it is possible to prevent short-
20 circuits between electrodes, prevent short-circuits
between separators, and prevent an increase of the
parasitic capacitance.

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